

## Octa- and nona-hydridosiliconium di- and tri-cations ( $\text{SiH}_8^{2+}$ and $\text{SiH}_9^{3+}$ ) containing eight- and nine-coordinate silicon atoms

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This paper is dedicated to our friend Prof. Kenneth Laali, on the occasion of his 65<sup>th</sup> birthday,  
and in recognition of his lifetime contributions to chemistry

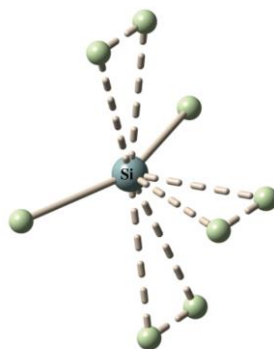
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### Abstract

Structures of octahydrido siliconium dication ( $\text{SiH}_8^{2+}$ ) and nonahydrido siliconium trication ( $\text{SiH}_9^{3+}$ ) were found to be computationally viable minima at the MP2/cc-pVTZ level and CCSD(T)/cc-pVTZ levels. Their structure has three and four two-electron three-center (2e-3c) bonds, respectively. The protonation of  $\text{SiH}_7^+$  to form the dication was found to be slightly endothermic by 4.1 kcal/mol at the CCSD(T)/cc-pVTZ//CCSD(T)/cc-pVTZ + ZPE level. Further protonation to form the trication was found to be highly endothermic by 162.2 kcal/mol. The deprotonation barriers of the ions were also computed.



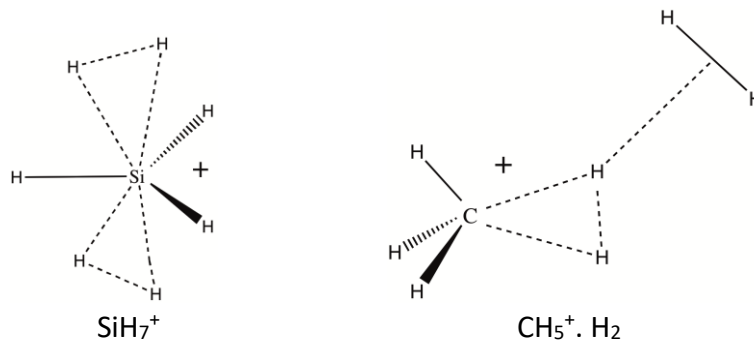
Octacoordinate hydrido siliconium dication

**Keywords:** Siliconium, dication, trication, higher coordinations

## Introduction

Higher coordinate<sup>1</sup> multicharged main group compounds are of substantial interest both theoretically<sup>2-6</sup> and experimentally.<sup>7</sup> Schmidbaur *et al.* have prepared a variety of monopositively charged higher coordinate gold complexes of main group elements.<sup>7</sup> They have also prepared dpositively charged carbon  $\{[(C_6H_5)_3PAu]_6C\}^{2+}$ ,<sup>8</sup> nitrogen  $\{[(C_6H_5)_3PAu]_5N\}^{2+}$ ,<sup>9</sup> phosphorus  $\{[(C_6H_5)_3PAu]_5P\}^{2+}$ ,<sup>10</sup> sulfur  $\{[(C_6H_5)_3PAu]_4S\}^{2+}$ ,<sup>11</sup> and oxygen  $\{[(o-CH_3C_6H_4)_3PAu]_4O\}^{2+}$ ,<sup>12</sup> and determined their X-ray structures. These represent isolobal analogs of  $CH_6^{2+}$ ,  $NH_5^{2+}$ ,  $PH_5^{2+}$ ,  $SH_4^{2+}$  and  $OH_4^{2+}$ , respectively.

Cao *et al.*<sup>13</sup> reported the first spectroscopic observation of  $SiH_7^+$ . Their IR data suggest that  $SiH_7^+$  is a symmetric complex ( $H_2 \cdots SiH_3 \cdots H_2$ ) with two two-electron three-center (2e-3c) bonds and with two two-electron two-center (2e-2c) bonds. This is in contrast to the species  $CH_7^+$ , which has been concluded, from both IR spectrum<sup>14</sup> and calculations,<sup>15</sup> to have a structure consisting of a  $H_2$  subunit weakly bound to one of the hydrogen atoms of the 2e-3c bond ( $CH_5^+ \cdot H_2$ ). Hu *et al.*<sup>16</sup> have also reported the calculated structures and Infrared spectrum of parent heptacoordinate siliconium ion,  $SiH_7^+$ . A similar structure has also been reported for  $GaH_7^+$ .<sup>17</sup>



**Scheme 1.** Structures of  $SiH_7^+$  and  $CH_5^+ \cdot H_2$ .

In continuation of our study of hypercoordinate compounds, we have now extended our theoretical investigations to the next higher homologues of  $SiH_7^+$  *i.e.*  $SiH_8^{2+}$  and  $SiH_9^{3+}$  ions at the MP2/cc-pVTZ and CCSD(T)/cc-pVTZ levels.

## Results and Discussion

Structures of **1** and **2** were optimized in the gas phase at the MP2/cc-pVTZ and CCSD(T)/cc-pVTZ levels. CCSD(T)/cc-pVTZ level structures are discussed throughout unless otherwise stated. Structure **1** was found to be a viable minimum (Figure 1) on the potential energy surface (PES) of  $SiH_8^{2+}$  at the both MP2/cc-pVTZ and CCSD(T)/cc-pVTZ levels. Computed energies are given in Table 1. Structure **1** contains three 2e-3c bonds involving the silicon atom and three hydrogen molecules and two 2e-2c bond involving the silicon atom and a hydrogen molecule. The ion can be considered as a complex between  $SiH_4^{2+}$  (protonated silicinium dication)<sup>18</sup> and two hydrogen molecules (Scheme 2). The Si-H bond distance (1.995 Å) of the axial 2e-3c bond units is considerably longer than that of the equatorial unit (1.842 Å). The possible stability of the eight-coordinate  $SiH_8^{2+}$  is due to the fact that the silicon can undergo  $sp^3d$  hybridization. In comparison, the eight-coordinate  $CH_8^{2+}$  ion was found not be a minimum on the PES. The dication dissociated into  $CH_6^{2+}$  and  $H_2$  upon

optimization. This is because, unlike silicon, carbon is unable to undergo  $sp^3d$  hybridization. Computed vibrational frequencies of the structure **1** are given in Table 2.

**Table 1.** Energies (-au), ZPE and relative energies (kcal/mol) of ions **1-4**

Structure no.	MP2/cc-pVTZ	ZPE (kcal/mol)	NIMAG <sup>b</sup>	rel. energy <sup>a</sup> (kcal/mol)	CCSD(T)/cc-pVTZ	rel. energy <sup>b</sup> (kcal/mol)
SiH <sub>7</sub> <sup>+</sup>	-292.82964	32.5	0	-4.8	-292.87141	-4.1
<b>1</b>	-292.82986	37.4	0	0.0	-292.87264	0.0
<b>2</b>	-292.57167	38.9	0	163.5	-292.61650	162.2
<b>3</b> <sub>TS</sub>	-292.71363	34.7	1	68.3		
<b>4</b> <sub>TS</sub>	-292.54590	36.2	1	177.0		

<sup>a</sup> Relative energy at MP2/cc-pVTZ//cc-pVTZ + ZPE level; <sup>b</sup> at the CCSD(T)/cc-pVTZ//CCSD(T)/cc-pVTZ + ZPE level.

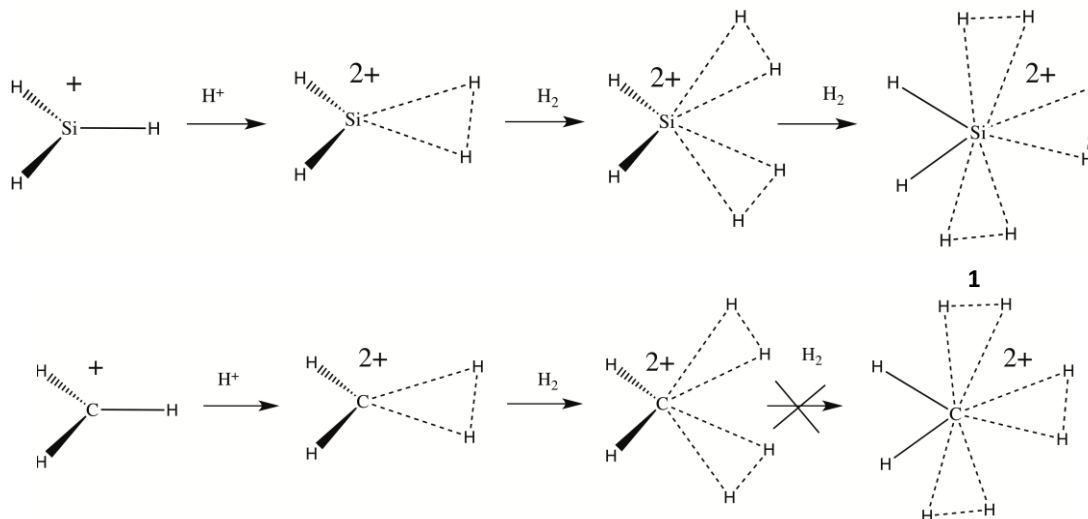
**Table 2.** Calculated frequencies<sup>a</sup> (cm<sup>-1</sup>) and IR intensities (km/mol) of **1**

MP2/cc-pVTZ		CCSD(T)/cc-pVTZ	
frequency	intensity	frequency	intensity
306	0	281	0
335	0	309	0
383	11	366	0
388	0	385	45
437	3	438	19
501	142	504	47
618	0	613	7
639	112	633	68
733	32	695	7
800	28	768	4
850	0	786	0
859	69	790	88
869	0	847	0
902	27	898	22
996	2	975	1
1079	60	1025	68
2307	16	2253	26
2398	142	2345	225
3779	295	3702	280
4005	721	3924	695
4042	6	3959	6

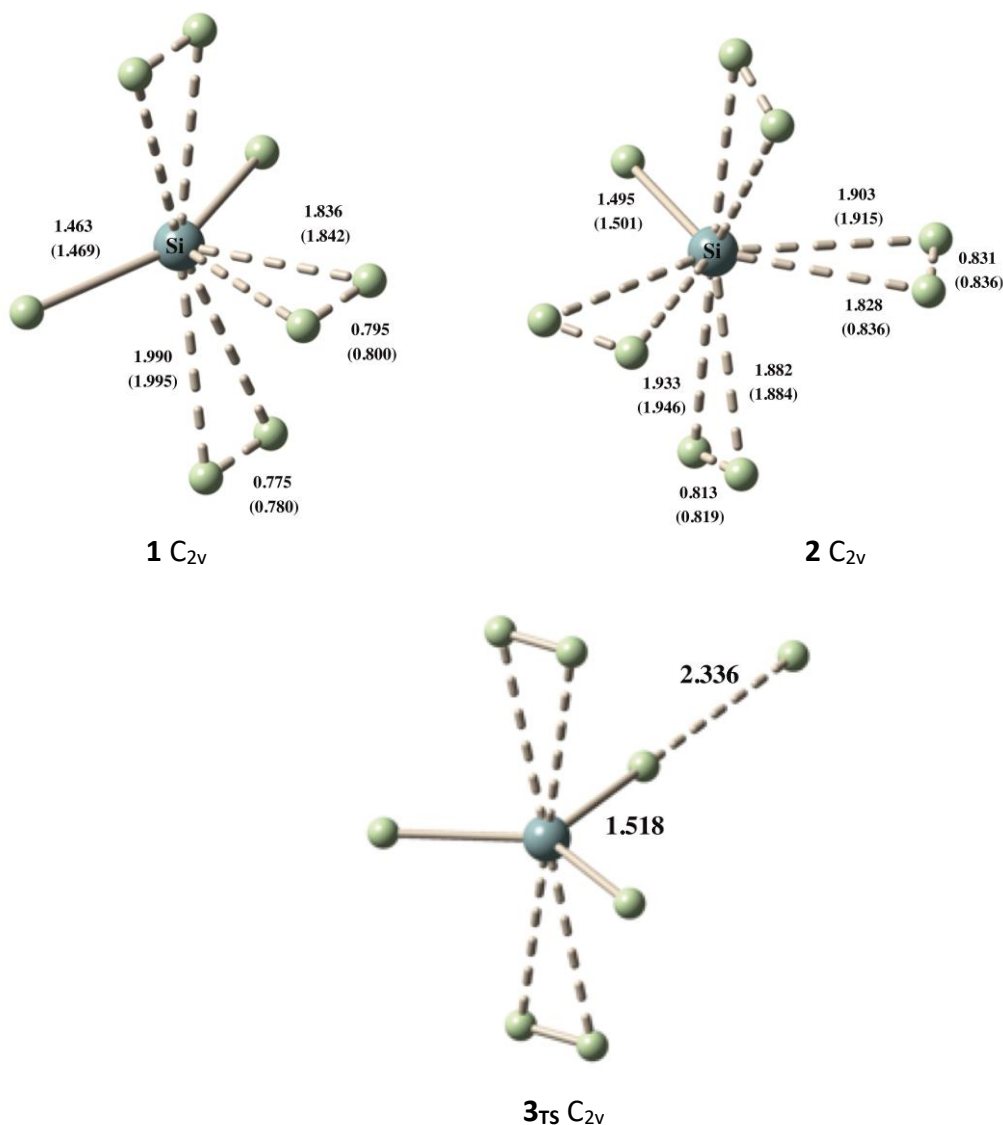
<sup>a</sup> Computed frequencies were not scaled.

Protonation of SiH<sub>7</sub><sup>+</sup> to form **1** was found to be endothermic by 4.8 kcal/mol at the MP2/cc-pVTZ//MP2/cc-pVTZ + ZPE level (4.1 kcal/mol at the CCSD(T)/cc-pVTZ//CCSD(T)/cc-pVTZ + ZPE level).

Transition structure,  $3_{TS}$  (Figure 1) for the deprotonation of **1** was also located. The structure  $3_{TS}$  lies 68.3 kcal/mol higher in energy than structure **1**. Thus the trication has also a high barrier for deprotonation.

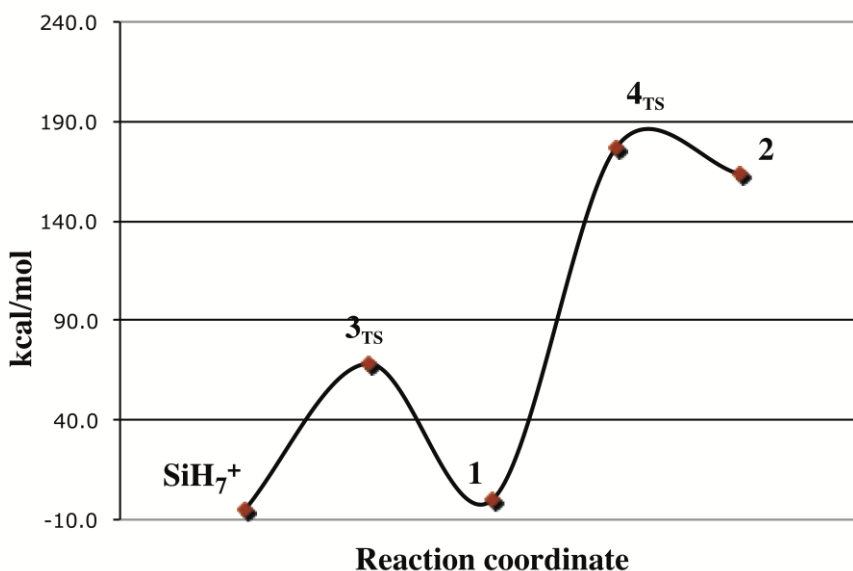


**Scheme 2.** Formation of  $\text{SiH}_8^{2+}$  and  $\text{CH}_6^{2+}$ .



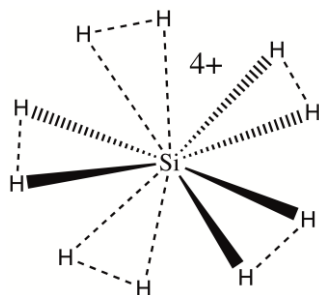
**Figure 1.** MP2/cc-pVTZ (CCSD(T)/cc-pVTZ) optimized structures of **1**, **2** and  $3_{TS}$ .

MP2/cc-pVTZ and CCSD(T)/cc-pVTZ optimizations show that the nine-coordinate siliconium structure **2** is also a minimum on the potential energy surface of  $\text{SiH}_9^{3+}$ . Tricationic structure **2** (Figure 1) contains four 2e-3c bonds involving the silicon atom and four hydrogen molecules and a 2e-2c bond involving the silicon atom and a hydrogen atom. The Si-H bond distances (1.946 and 1.884 Å) of the axial 2e-3c bond units are slightly longer than those of the equatorial units (1.915 and 1.836 Å). Charge-charge repulsions in the trications are substantial. However, the bonding interactions are strong enough to counter charge-charge repulsions rendering them remarkably stable. Dissociation of **2** into **1** and  $\text{H}^+$  was calculated to be very exothermic by 163.5 kcal/mol at the MP2/cc-pVTZ//MP2/cc-pVTZ + ZPE level (162.2 kcal/mol at the CCSD(T)/cc-pVTZ//CCSD(T)/cc-pVTZ + ZPE level). The transition structure **4<sub>TS</sub>** for the dissociation lies just 13.5 kcal/mol higher in energy than structure **2**. This shows that the trication **2**, if formed will dissociate spontaneously into **1** and  $\text{H}^+$ . Potential energy surface of **1** and **2** calculated MP2/cc-pVTZ//MP2/cc-pVTZ + ZPE level is depicted in Figure 2.



**Figure 2.** Potential energy surface of **1** and **2**.

We also searched for any minimum-energy structures of deca-coordinate siliconium ion,  $\text{SiH}_{10}^{4+}$ . At the MP2/cc-pVTZ level no minimum could be found on the PES of  $\text{SiH}_{10}^{4+}$  (including a structure with five 2e-3c bonds as shown in Scheme 3). Thus in  $\text{SiH}_{10}^{4+}$  charge-charge repulsion may have reached its prohibitive limit.



**Scheme 3.** Possible structure of  $\text{SiH}_{10}^{4+}$ .

## Conclusions

The present calculational study at the MP2/cc-pVTZ and CCSD(T)/cc-pVTZ levels shows that the octahydrido-silconium dication ( $\text{SiH}_8^{2+}$ ) **1** and nonahydridosilconium trication ( $\text{SiH}_9^{3+}$ ) **2** are viable energy minima. Structures **1** and **2** were found to be stabilized by three and four 2e-3c bonds, respectively. The protonation of  $\text{SiH}_7^+$  to form **1** was calculated to be slightly endothermic by about 5 kcal/mol. Charge-charge repulsions in these di- and tri-cations are substantial. However, the bonding interactions are strong enough to counter charge-charge repulsions rendering them remarkably stable.

## Experimental Section

### Calculations

Geometry optimizations and frequency calculations were carried out with the Gaussian 09 program.<sup>19</sup> Vibrational frequencies at the MP2/cc-pVTZ//MP2/cc-pVTZ level were used to characterize stationary points as minima (NIMAG (number of imaginary frequency) = 0 or transition state NIMAG = 1) and to compute zero point vibrational energies (ZPE), which were scaled by a factor of 0.96.<sup>20</sup> CCSD(T)/cc-pVTZ optimizations and frequency calculations have been performed with the CFOUR program.<sup>21,22</sup>

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## References

1. Olah, G. A.; Prakash, G. K. S.; Wade, K.; Molnar, A.; Williams, R. E. *Hypercarbon Chemistry*, John Wiley & Sons, New York, 2011.  
<https://doi.org/10.1002/9781118016466>
2. Olah, G. A.; Rasul, G. *Acc. Chem. Res.* **1997**, *30*, 245.  
<https://doi.org/10.1021/ar960103f>
3. Haberlen, O. D.; Schmidbaur, H.; Rosch, N. *J. Am. Chem. Soc.* **1994**, *115*, 8241.  
<https://doi.org/10.1021/ja00097a034>
4. Gorling, A.; Rosch, N.; Ellis, D. E.; Schmidbaur, H. *Inorg. Chem.* **1991**, *30*, 3986.  
<https://doi.org/10.1021/ic00021a005>
5. Schreiner, P. R.; Schaefer, H. F.; Schleyer, P. v. R. *Advances in Gas Phase Ion Chemistry*, JAI Press Inc., 1996, p-125.
6. Schreiner, P. R.; Schaefer, H. F.; Schleyer, P. v. R. *J. Chem. Phys.* **1995**, *103*, 5565.  
<https://doi.org/10.1063/1.470540>
7. Schmidbaur, H. *Chem. Soc. Rev.*, **1995**, *24*, 391.  
<https://doi.org/10.1039/cs9952400391>
8. Scherbaum, F.; Grohmann, A.; Huber B.; Krüger, C.; Schmidbaur, H. *Angew. Chem. Int. Ed. Engl.* **1988**, *27*, 1544.  
<https://doi.org/10.1002/anie.198815441>
9. Grohmann, A.; Riede, J.; Schmidbaur, H. *Nature* **1990**, *345*, 140.

- <https://doi.org/10.1038/345140a0>
10. Schmidbaur, H.; Beruda, H.; Zeller, E. *Phosphorus, Sulfur Silicon* **1994**, *87*, 245.  
<https://doi.org/10.1080/10426509408037457>
  11. Zeller, E.; Beruda, H.; Schmidbaur, H. *Inorg. Chem.* **1993**, *32*, 3203.  
<https://doi.org/10.1021/ic00067a002>
  12. Schmidbaur, H.; Hofreiter, S.; Paul, M. *Nature* **1995**, *377*, 503.  
<https://doi.org/10.1038/377503a0>
  13. Cao, Y.; Choi, J. H.; Haas, B. M.; Johnson, M. S.; Okumura, M. *J. Phys. Chem.* **1993**, *97*, 5215.  
<https://doi.org/10.1021/j100122a008>
  14. Boo, D. W.; Lee, Y. T. *Chem. Phys. Lett.* **1993**, *211*, 358.  
[https://doi.org/10.1016/0009-2614\(93\)87073-C](https://doi.org/10.1016/0009-2614(93)87073-C)
  15. Kim, S. J.; Schreiner, P. R.; Schleyer, P. v. R.; Schaefer, H. F. *J. Phys. Chem.* **1993**, *97*, 12232.  
<https://doi.org/10.1021/j100149a023>
  16. Hu, C.-H.; Schreiner, P. R.; Schleyer, P. v. R.; Schaefer, H. F. *J. Phys. Chem.* **1994**, *98*, 5040-5043.  
<https://doi.org/10.1021/j100070a015>
  17. So, S. P. *J. Phys. Chem.* **1996**, *100*, 5250.  
<https://doi.org/10.1021/jp953020+>
  18. Rasul, G.; Prakash, G. K. S.; Olah, G. A. *Inorg. Chem.* **1999**, *38*, 4132.  
<https://doi.org/10.1021/ic9901620>
  19. Frisch, M. J. *et al. Gaussian 09*, Revision A.02, Gaussian, Inc., Wallingford CT, 2009.
  20. Alecu, I. M.; Zheng, J.; Zhao, Y.; Truhlar, D. G. *J. Chem. Theory Comput.* **2010**, *6*, 2872.  
<https://doi.org/10.1021/ct100326h>
  21. CFOUR, a quantum chemical program package, Stanton, J. F.; Gauss, J.; Harding, M. E.; Szalay, P. G. with contributions from Auer, A. A.; Bartlett, R. J.; Benedikt, U.; Berger, C.; Bernholdt, D. E.; Bomble, Y. J.; Cheng, L.; Christiansen, O.; Heckert, M.; Heun, O.; Huber, C.; Jagau, C.; Jonsson, D.; Jusélius, J.; Klein, K.; Lauderdale, W. J.; Mathews, D. A.; Metzroth, T.; O'Neill, D. P.; Price, D. R.; Prochnow, E.; Ruud, K.; Schiffmann, F.; Schwalbach, W.; Stopkowitz, S.; Tajti, A.; Vázquez, J.; Wang, F.; Watts, J. D.; and the integral packages MOLE-CULE (Almlöf, J and Taylor, P. R.), PROPS (Taylor, P. R.), ABACUS (Helgaker, T.; Aa, H. J.; Jensen H. J. A.; Jørgensen, P.; Olsen, J.), and ECP routines (Mitin, A. V.; Wüllen, C. van), **2010**.
  22. Harding, M. E.; Metzroth, T.; Gauss, J.; Auer, A. A. *J. Chem. Theory Comput.* **2008**, *4*, 64.  
<https://doi.org/10.1021/ct700152c>